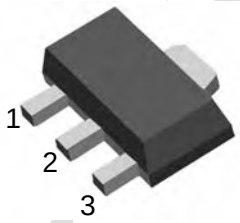
BCX55 TRANSISTOR (NPN)

SOT-89

1. BASE
2. COLLECTOR
3. EMITTER



FEATURES

Power dissipation

$P_{CM:}$ 0.5 W (Tamb=25℃)

Collector current

$I_{CM:}$ 1 A

Collector-base voltage

$V_{(BR)CBO}$: 60 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic=100μA, I_E=0	60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= 10mA , I_B=0	60		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=10μA, I_C=0	5		V
Collector cut-off current	I_{CBO}	V_{CB}=30V, I_E=0		0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5 V, I_C=0		0.1	μA
DC current gain **BCX55** **BCX55-10** **BCX55-16**	$h_{FE(1)}$	V_{CE}=2V, I_C= 150mA	63 63 100	250 160 250	
	$h_{FE(2)}$	V_{CE}=2V, I_C= 5mA	40		
	$h_{FE(3)}$	V_{CE}=2V, I_C= 500mA	25		
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=500 mA, I_B= 50mA		0.5	V
Base-emitter voltage	$V_{BE(ON)}$	I_C= 500 mA, V_{CE}=2V		1	V
Transition frequency	f_T	V_{CE}= 10V, I_C= 50mA f = 100MHz	130		MHz

DEVICE MARKING	BCX55=BE BCX55-10=BG BCX55-16=BM